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# Silicon Carbide Schottky Diode

1700 V, 25 A

# **NDSH25170A**

#### **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 506 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Halogen Free/BFR Free and are RoHS Compliant

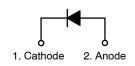
#### **Applications**

- SMPS, Solar Inverter, UPS
- Power Switching Circuits

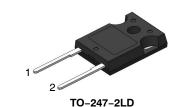


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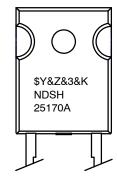


**Schottky Diode** 



TO-247-2LD CASE 340DA

#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code &K = Lot Code

NDSH25170A = Specific Device Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## **ABSOLUTE MAXIMUM RATINGS** ( $T_J = 25$ °C unless otherwise noted)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	1700	V	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)	506	mJ	
lF	Continuous Rectified Forward Current @ T <sub>C</sub> < 153°C		25	Α
	Continuous Rectified Forward Current @ T <sub>C</sub> < 135°C		35	
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	1435	Α
		T <sub>C</sub> = 150°C, 10 μs	1428	Α
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	220	А
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	66	Α
Ptot	Power Dissipation	T <sub>C</sub> = 25°C	385	W
		T <sub>C</sub> = 150°C	64	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ hetaJC}$	Thermal Resistance, Junction to Case, Max	0.39	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 25 A, T <sub>J</sub> = 25°C	-	1.50	1.75	V
		I <sub>F</sub> = 25 A, T <sub>J</sub> = 125°C	_	1.95	2.35	
		I <sub>F</sub> = 25 A, T <sub>J</sub> = 175°C	=	2.32	2.8	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 1700 V, T <sub>J</sub> = 25°C	=	0.08	40	μΑ
		V <sub>R</sub> = 1700 V, T <sub>J</sub> = 125°C	-	0.58	60	
		V <sub>R</sub> = 1700 V, T <sub>J</sub> = 175°C	-	4.24	100	
Q <sub>C</sub>	Total Capacitive Charge	V = 800 V	-	169	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	2025	-	pF
		V <sub>R</sub> = 400 V, f = 100 kHz	-	155	-	
		V <sub>R</sub> = 800 V, f = 100 kHz	_	109	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **ORDERING INFORMATION**

Part Number	Top Marking	Package	Shipping
NDSH25170A	NDSH25170A	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube

<sup>1.</sup>  $E_{AS}$  of 506 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 0.5 mH,  $I_{AS} = 45$  A, V = 50 V.

## **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

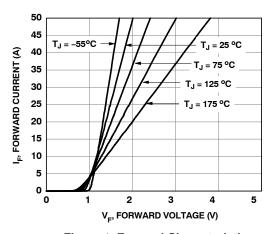


Figure 1. Forward Characteristics

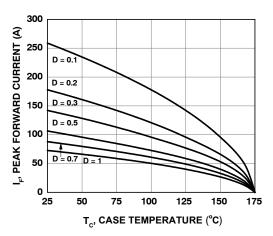


Figure 3. Current Derating

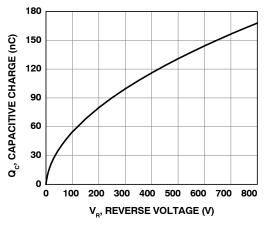


Figure 5. Capacitive Charge vs. Reverse Voltage

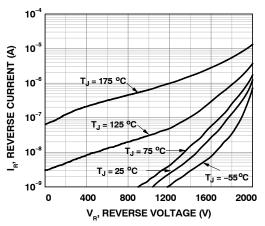


Figure 2. Reverse Characteristics

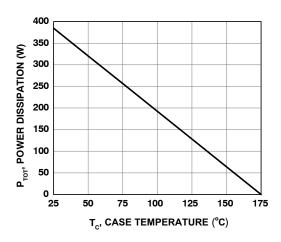


Figure 4. Power Derating

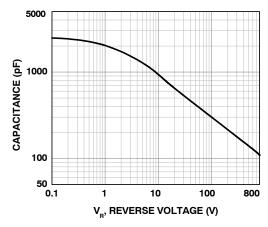


Figure 6. Capacitance vs. Reverse Voltage

## **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

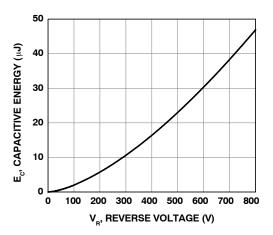


Figure 7. Capacitance Stored Energy

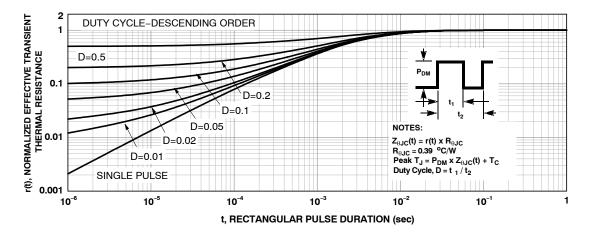
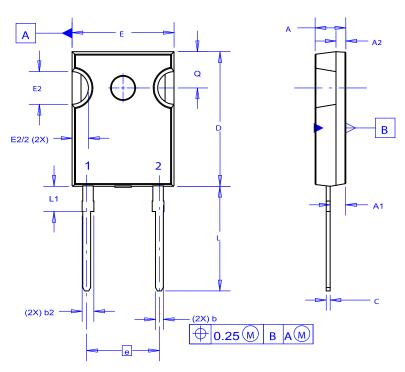


Figure 8. Junction-to-Case Transient Thermal Response Curve

## **PACKAGE DIMENSIONS**

TO-247-2LD CASE 340DA **ISSUE A** 

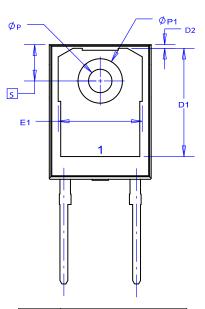


## NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

  B. ALL DIMENSIONS ARE IN MILLIMETERS.

- C. DRAWING CONFORMS TO ASME Y14.5 2009.
  D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.



DIM	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	4.58	4.70	4.82		
A1	2.20	2.40	2.60		
A2	1.40	1.50	1.60		
b	1.17	1.26	1.35		
b2	1.53	1.65	1.77		
С	0.51	0.61	0.71		
D	20.32	20.57	20.82		
D1	13.08	?	~		
D2	0.51	0.93	1.35		
Е	15.37	15.62	15.87		
E1	12.81	l	~		
E2	4.96	5.08	5.20		
е	ł	11.12	?		
L	15.75	16.00	16.25		
L1	3.69	3.81	3.93		
ØΡ	3.51	3.58	3.65		
ØP1	6.60	6.80	7.00		
Q	5.34	5.46	5.58		
S	5.34	5.46	5.58		

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Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

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Largest Supplier of Electrical and Electronic Components

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Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

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BAS16E6433HTMA1 BAT 54-02LRH E6327 NSR05F40QNXT5G NTE555 JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W SK310-T

SK32A-LTP SK34B-TP SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP SK33B-TP SK38B-TP NRVBM120LT1G NTE505 NTSB30U100CT-1G SS15E-TP VS-6CWQ10FNHM3 ACDBA1100LR-HF ACDBA1200-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF ACDBA340-HF ACDBA260LR-HF

ACDBA1100-HF SK310B-TP MA4E2502L-1246 MA4E2502H-1246 NRVBM120ET1G NSR01L30MXT5G NTE573 NTE6081 SB560 PMAD1108-LF